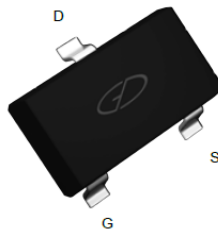
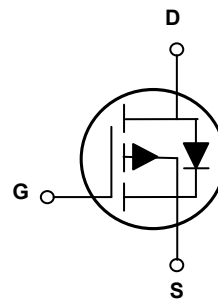


## Main Product Characteristics

$V_{(BR)DSS}$	-30V
$R_{DS(ON)}$	80mΩ
$I_D$	-3.0A



SOT-23



Schematic Diagram

## Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



## Description

The SSF3365 utilizes the latest techniques to achieve ultrahigh cell density and low on-resistance. These features make this device extremely efficient and reliable for use in battery protection, load switch, power management and a wide variety of other applications.

## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	$I_D (25^\circ\text{C})$	-3	A
	$I_D (70^\circ\text{C})$	-2.5	A
	$I_{DM}$	-12	A
Maximum Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	°C/W
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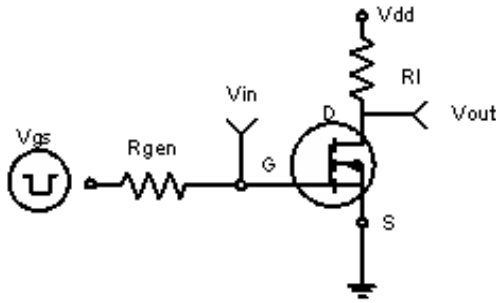
**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$			-1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
<b>ON CHARACTERISTICS (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1			V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3A$		64	80	m $\Omega$
		$V_{GS}=-4.5V, I_D=-2.5A$		100	140	
Forward Transconductance	$g_{FS}$	$V_{DS}=-10V, I_D=-3A$	3			S
<b>DYNAMIC CHARACTERISTICS (Note 4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$		600		PF
Output Capacitance	$C_{oss}$			150		PF
Reverse Transfer Capacitance	$C_{rss}$			95		PF
<b>SWITCHING CHARACTERISTICS (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-1A$ $V_{GS}=-10V, R_{GEN}=6\Omega$		10		nS
Turn-on Rise Time	$t_r$			9		nS
Turn-Off Delay Time	$t_{d(off)}$			25		nS
Turn-Off Fall Time	$t_f$			8		nS
Total Gate Charge	$Q_g$	$V_{DS}=-15V, I_D=-3A, V_{GS}=-10V$		10		nC
Gate-Source Charge	$Q_{gs}$			2		nC
Gate-Drain Charge	$Q_{gd}$			2		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-1.25A$			-1.2	V

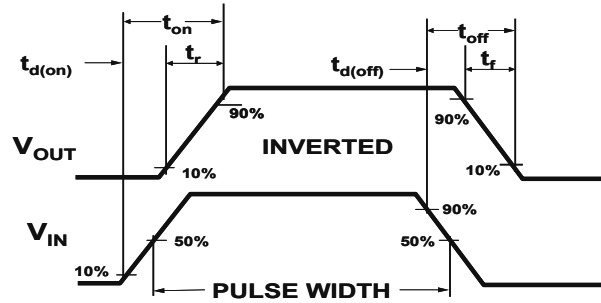
**NOTES:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in<sup>2</sup> FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

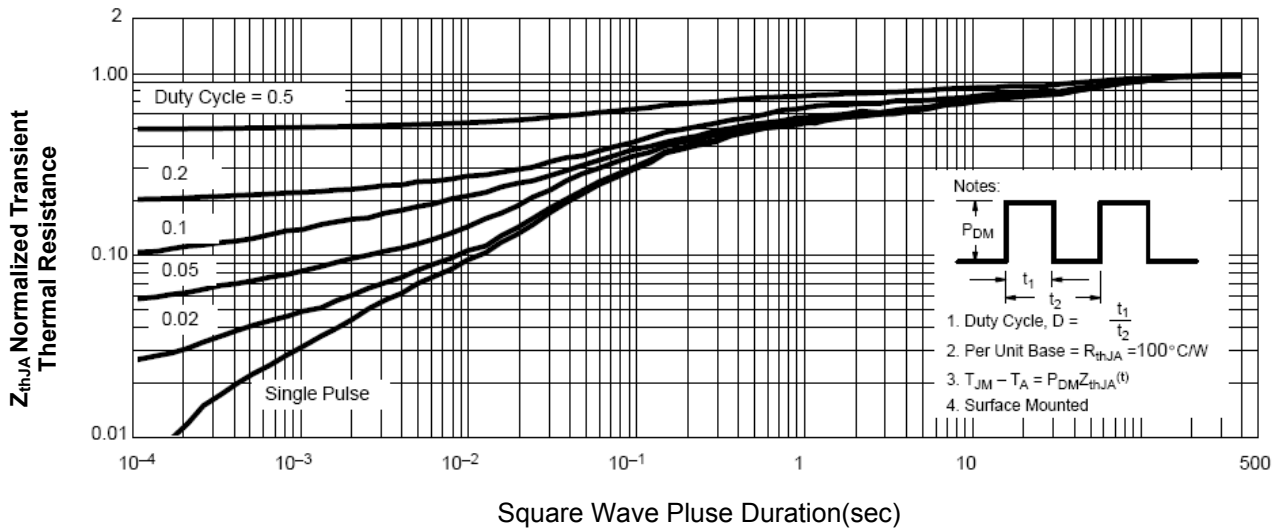
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



**Figure 1. Switching Test Circuit**



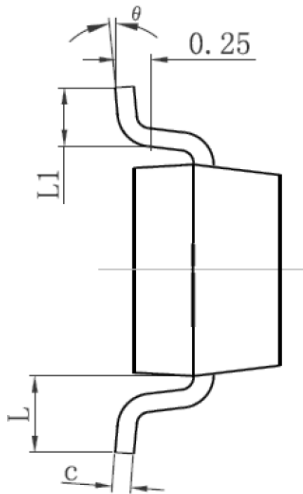
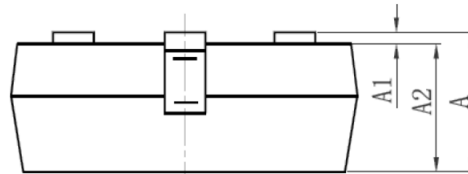
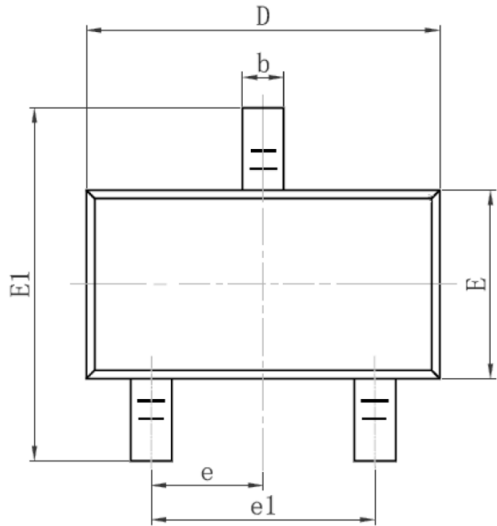
**Figure 2. Switching Waveforms**



**Figure 3. Normalized Maximum Transient Thermal Impedance**

**SOT-23 PACKAGE INFORMATION**

Dimensions in Millimeters (UNIT: mm)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
<b>A</b>	<b>0.900</b>	<b>1.150</b>
<b>A1</b>	<b>0.000</b>	<b>0.100</b>
<b>A2</b>	<b>0.900</b>	<b>1.050</b>
<b>b</b>	<b>0.300</b>	<b>0.500</b>
<b>c</b>	<b>0.080</b>	<b>0.150</b>
<b>D</b>	<b>2.800</b>	<b>3.000</b>
<b>E</b>	<b>1.200</b>	<b>1.400</b>
<b>E1</b>	<b>2.250</b>	<b>2.550</b>
<b>e</b>	<b>0.950TYP</b>	
<b>e1</b>	<b>1.800</b>	<b>2.000</b>
<b>L</b>	<b>0.550REF</b>	
<b>L1</b>	<b>0.300</b>	<b>0.500</b>
<b>θ</b>	<b>0°</b>	<b>8°</b>

**NOTES**

1. All dimensions are in millimeters..
2. Tolerance ±0.10mm (4 mil) unless otherwise specified.
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.